Device Modeling Report

COMPONENTS: TRANSISTOR
PART NUMBER: US6T6TR
MANUFACTURER: ROHM
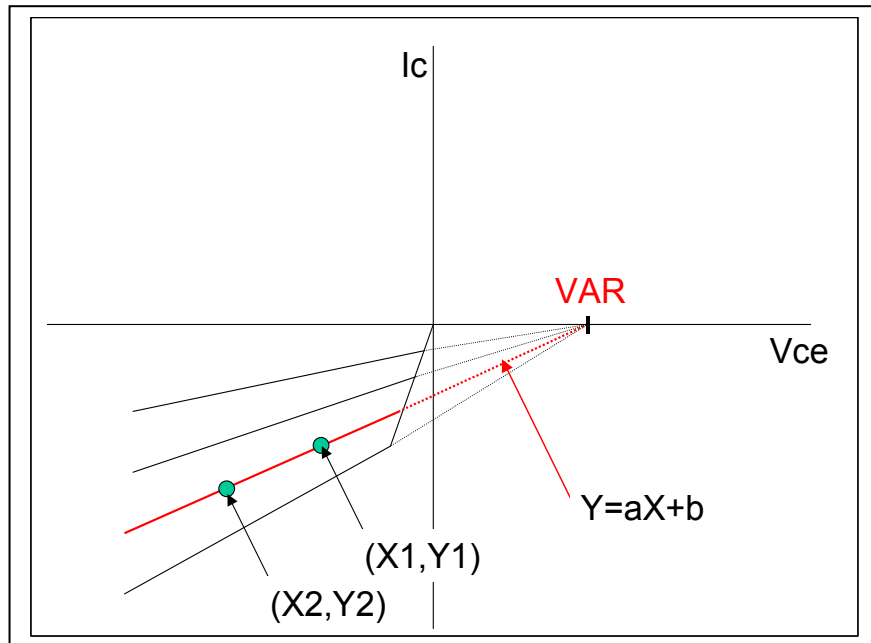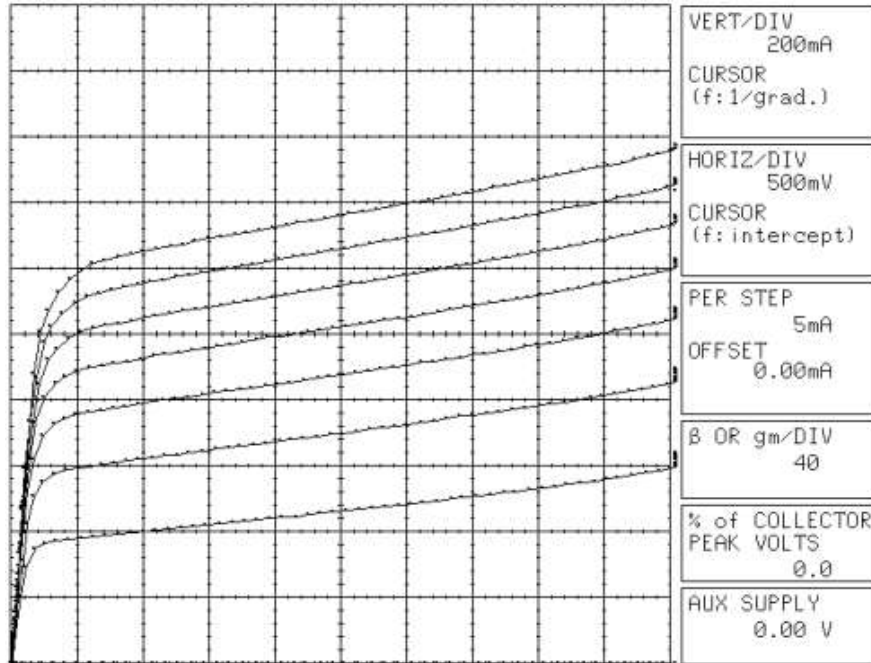
Bee Technologies Inc.

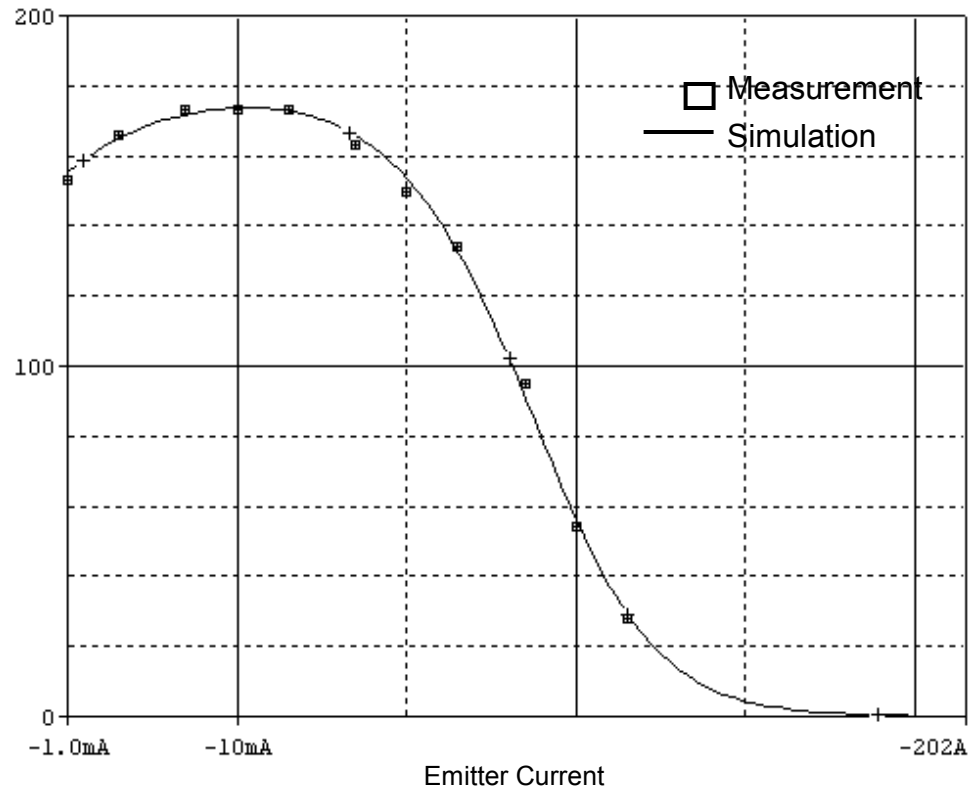## TRANSISTOR MODEL

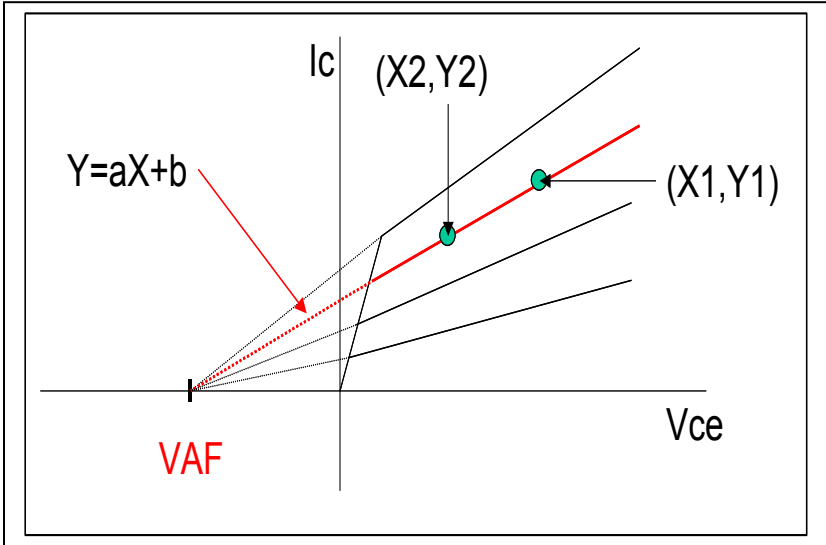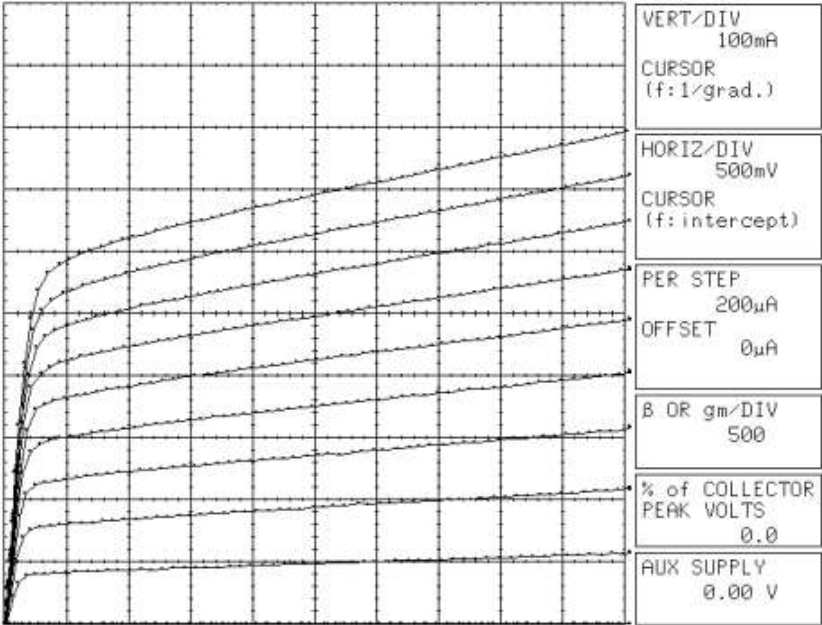| PSpice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
NF	Forward Current Emission Coefficient
VAF	Forward Early Voltage
IKF	Forward Beta Roll-off Knee Current
ISE	Non-ideal Base-Emitter Diode Saturation Current
NE	Non-ideal Base-Emitter Diode Emission Coefficient
BR	Ideal Maximum Reverse Beta
NR	Reverse Emission Coefficient
VAR	Reverse Early Voltage
IKR	Reverse Beta Roll-off Knee Current
ISC	Non-ideal Base-Collector Diode Saturation Current
NC	Non-ideal Base-Collector Diode Emission Coefficient
NK	Forward Beta Roll-off Slope Exponent
RE	Emitter Resistance
RB	Base Resistance
RC	Series Collector Resistance
CJE	Zero-bias Emitter-Base Junction Capacitance
VJE	Emitter-Base Junction Potential
MJE	Emitter-Base Junction Grading Coefficient
CJC	Zero-bias Collector-Base Junction Capacitance
VJC	Collector-base Junction Potential
MJC	Collector-base Junction Grading Coefficient
FC	Coefficient for Onset of Forward-bias Depletion Capacitance
TF	Forward Transit Time
XTF	Coefficient for TF Dependency on Vce
VTF	Voltage for TF Dependency on Vce
ITF	Current for TF Dependency on Ic
PTF	Excess Phase at f=1/2pi*TF
TR	Reverse Transit Time
EG	Activation Energy
XTB	Forward Beta Temperature Coefficient
XTI	Temperature Coefficient for IS

Reverse

Reverse Early Voltage Characteristic

VERT/DIV	200mA
CURSOR (f:1/grad.)	
HORIZ/DIV	500mV
CURSOR (f:intercept)	
PER STEP	5mA
OFFSET	0.00mA
B OR gm/DIV	40
% of COLLECTOR PEAK VOLTS	0.0
AUX SUPPLY	0.00 V

Ic

Vce

VAR

Y=aX+b

(X1,Y1)
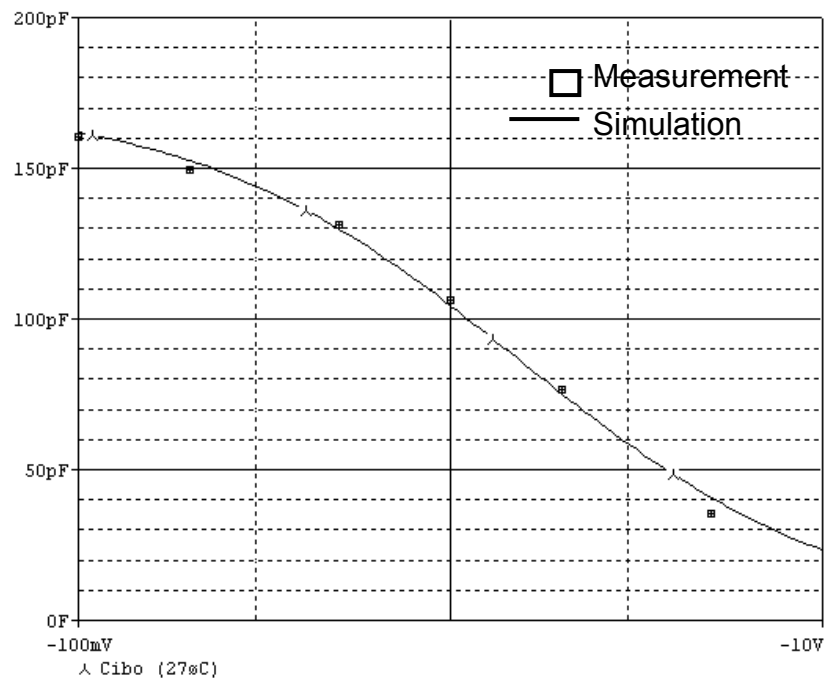
(X2,Y2)

Reverse DC Beta Characteristic (Ie vs. hFE)

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Forward Early Voltage Characteristic


```
VERT/DIV
       100mA
CURSOR
(f:1/grad.)

HORIZ/DIV
       500mV
CURSOR
(f:intercept)

PER STEP
       200µA
OFFSET
       0µA

ß OR gm/DIV
       500

% of COLLECTOR
PEAK VOLTS
       0.0

AUX SUPPLY
       0.00 V
```

C-B Capacitance Characteristics

60pF

40pF

20pF

0F

-100mV   -50V

□ Measurement
— Simulation

○ Cobo (27øC)

E-B Capacitance Characteristics

200pF

150pF

100pF

50pF

0F

-100mV   -10V

□ Measurement
— Simulation

人 Cibo (27øC)

Transistor h_{FE}-I_C Characteristics

```
□ IC(X_U1.Q_Q1)/ I(U1:3)
                    IC(X_U1.Q_Q1)
```

Evaluation Circuit

Comparison Graph

Ic(A)	hFE		Error(%)
	Measurement	Simulation	
-0.001	580.000	578.681	-0.227
-0.002	580.000	576.619	-0.583
-0.005	575.000	572.750	-0.391
-0.010	565.000	568.268	0.578
-0.020	560.000	561.064	0.190
-0.050	535.000	543.381	1.567
-0.100	514.000	519.277	1.027
-0.200	480.000	481.871	0.390
-0.500	425.000	411.094	-3.272
-1.000	365.000	346.954	-4.944
-2.000	295.000	281.115	-4.707

V_{CE(Sat)}-I_C Characteristics

$V_{CE(Sat)}$-I_C Characteristics

```
-10V

-1.0mV
   -1.0mA                                    -10A
      □ VC(X_U1.Q_Q1)
                   IC(X_U1.Q_Q1)
```

Evaluation Circuit

VC

F1
F
20
0Adc
I1

U1
US6T6TR

0

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Comparison Graph

Simulation Result

IC(A)	VCE(sat)(V)		Error(%)
	Measurement	Simulation	
-0.001	-0.0043	-0.0043	0.4651
-0.002	-0.0045	-0.0045	0.4444
-0.005	-0.0050	-0.0050	0.8000
-0.010	-0.0058	-0.0058	0.1724
-0.020	-0.0071	-0.0071	0.4225
-0.050	-0.0110	-0.0109	-0.9091
-0.100	-0.0165	-0.0163	-1.2121
-0.200	-0.0270	-0.0263	-2.4556
-0.500	-0.0565	-0.0548	-2.9735
-1.000	-0.1000	-0.1007	0.7000
-2.000	-0.1850	-0.1907	3.0924

V_{BE(Sat)}-I_C Characteristics

$V_{BE(Sat)}$-I_C Characteristics

Circuit Simulation Result


```
-10V
                                                                    VB(X_U1.Q_Q1)
-1.0mV
   -1.0mA                                                           -10A
```
□ VB(X_U1.Q_Q1)

IC(X_U1.Q_Q1)

Evaluation Circuit

VC

F1
F
20

0Adc

I1

U1
US6T6TR

0

Comparison Graph

Simulation Result

IC(A)	VBE(sat)(V)		Error(%)
	Measurement	Simulation	
-0.001	-0.770	-0.740	-3.896
-0.002	-0.785	-0.758	-3.439
-0.005	-0.795	-0.782	-1.635
-0.010	-0.815	-0.800	-1.840
-0.020	-0.825	-0.843	2.182
-0.050	-0.850	-0.862	1.412
-0.100	-0.870	-0.862	-0.920
-0.200	-0.890	-0.882	-0.899
-0.500	-0.910	-0.911	0.110
-1.000	-0.935	-0.935	0.000
-2.000	-0.960	-0.964	0.417

Switching Characteristics

Circuit simulation result

Evaluation circuit

Simulation result

	Measurement	Simulation	%Error
t$_f$ (ns)	50.000	48.158	-3.684
t$_{stg}$ (ns)	112.000	110.443	-1.390

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F$_t$ - I$_C$ Characteristics

Circuit Simulation Result

□ ZeroCross(DB(I(U2:2)))

V_Ic

Evaluation Circuit

Simulation Result

IC(A)	FT(MHz)		Error(%)
	Measurement	Simulation	
-0.200	405.000	420.743	3.887

Output Characteristics

Evaluation Circuit

Output Characteristics

Reference

VERT/DIV 100mA	
CURSOR (f:1/grad.)	
HORIZ/DIV 500mV	
CURSOR (f:intercept)	
PER STEP 200µA	
OFFSET 0µA	
B OR gm/DIV 500	
% of COLLECTOR PEAK VOLTS 0.0	
AUX SUPPLY 0.00 V	